INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(Not for submission under 37 CFR 1.99)

Application Number		10791334				
Filing Date		2004-03-01				
First Named Inventor	Gı Yo	ul Km				
Art Unit		1792				
Examiner Name	David	David P. Turocy				
Attornou Docket Number		40004551 0025 002				

		Remove				
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear
	1	4389973		1983-06-28	Suntola, T.S. et al.	
	2	5281274		1994-01-25	Yoder, Max N.	
	3	5855675		1997-03-03	Doering, Kenneth et al.	
	4	5879459		1999-03-09	Gadgil, Prasad N. et al.	
	5	6042652		2000-03-28	Hyun, Kwang-soo et al.	
	6	6174377		2001-01-16	Doering, Kenneth et al.	
	7	6387185		2002-05-14	Doering, Kenneth et al.	
	8	6503330		2003-01-07	Sneh, Ofer et al.	

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)

Application Number		10791334			
Filing Date		2004-03-01			
First Named Inventor	Gı Yo	Si Youl Kim			
Art Unit		1792			
Examiner Name	David	P. Turocy			
Attorney Docket Number		40004551-0025-002			

	9	6270572		2001-08	3-07	Kım, Yeong-kwan et al.					
	10	6306216		2001-10-23		Kim, Yong II el	tal.				
If you wish to add additional U.S. Patent citation information please click the Add button.											
U.S.PATENT APPLICATION PUBLICATIONS Remove											
Examiner Initial*	Cite N	Cite No Publication Kind Number Code ¹ Da		Publica Date	ition	name of Patentee of Applicant			Pages,Columns,Lines where Relevant Passages or Releva Figures Appear		
	1	20050260348		2005-11-24 Lee,		Lee, Jung-hyun et al.					
If you wis	h to ad	d additional U.S. Publi	shed Ap	plication	citatio	n information p	lease click the Adi	buttor	. Add		
				FOREIG	SN PAT	ENT DOCUM	ENTS		Remove		
Examiner Initial*		Foreign Document Cou Number ³ Cod			Kind Code ⁴	Publication Date	Applicant of cited		Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear		T4
	1										
If you wis	h to ad	d additional Foreign P	atent Do	cument	citation	information pl	lease click the Add	button	Add		_
			NON	I-PATE	NT LITE	RATURE DO	CUMENTS		Remove		
Examiner Initials* Cite Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue numbor(s), publisher, city and/or country where published.								T5			
	1	S.M. GEORGE 'Alomic Layer Deposition: An Overview', Chem. Rev., 110, pp. 111-131 (2010)									
		R.A. WIND and S.M. GEORGE "Duartz Crystal Microbalance Studies of AIZO3 Atomic Layer Deposition Using Trimethylarumnum and Water at 125"C", J. Phys. Chem. A, 114, pp. 1281-1289 (2010)									

	3	JW, ELAM et al., "Viscous Flow Reactor with Quartz Crystal Microbalance for Thin Film Growth by Atomic Layer Deposition", Rev. Sci. Instrum., 73, pp. 2981-2987 (2002)				
	4	A.W. OTT et al., "A/203 Thin Film Growth on Si(100) Using Binary Reaction Sequence Chemistry", Thin Solid Films, 292, pp. 135-144 (1997)				
	5	M.D. GRONER et al., "Low Temperature AI2O3 Atomic Layer Deposition", Chem. Mater., 16, pp. 639-645 (2004)				
If you wish to add additional non-patent literature document citation information please click the Add button Add						

citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 See Kind Codes of USPTO Patent Documents at www.USPTO.GDM or MEEP 901.04. ² Entire office that issued the document, by the two-letter code (WIPD Standard STS.). ² For Japanese spelard documents, we includate or the system of the engine of the disposant must precise the season in motion of the patent document. ² For for disposanties by the spengrades symptoms as includated on the document under WIPD Standard STS. ² For patent spengrades spends as includated on the document under WIPD Standard STS. ² For patent spends as including the spengrades spends are included in the document under WIPD Standard STS. ² For patent spends are included in the document under WIPD Standard STS. ² For patent spends are included in the document under WIPD Standard STS. ² For patent spends are included in the spend